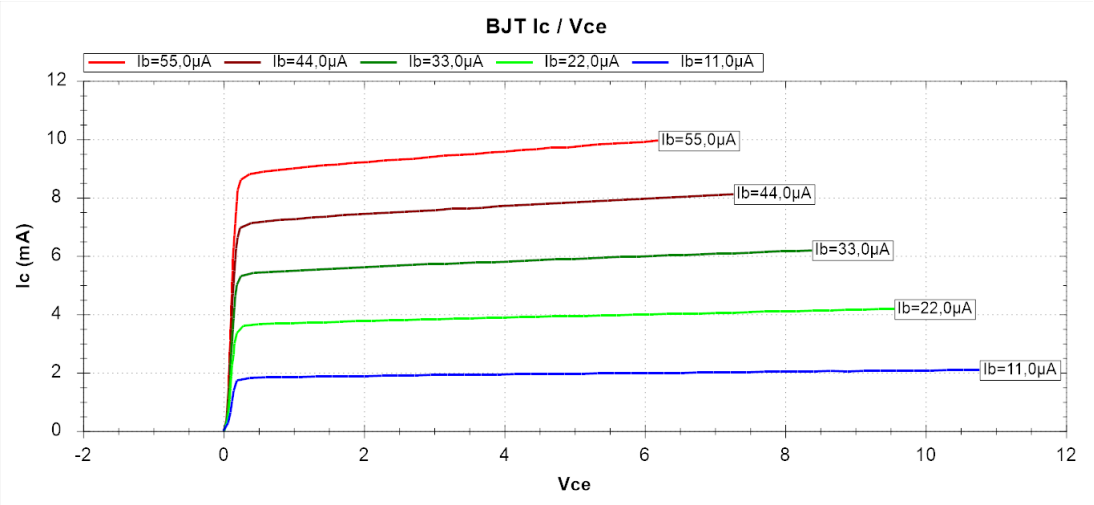
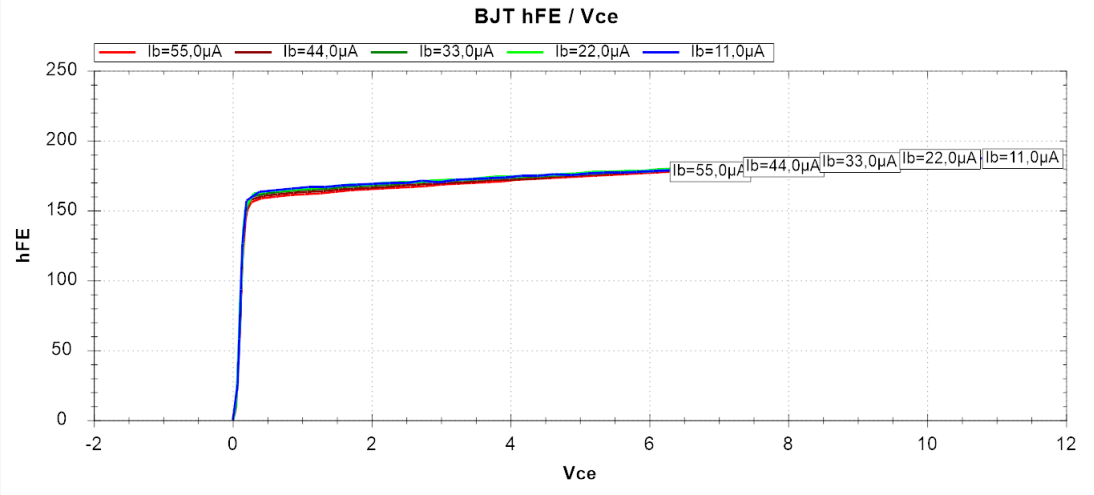
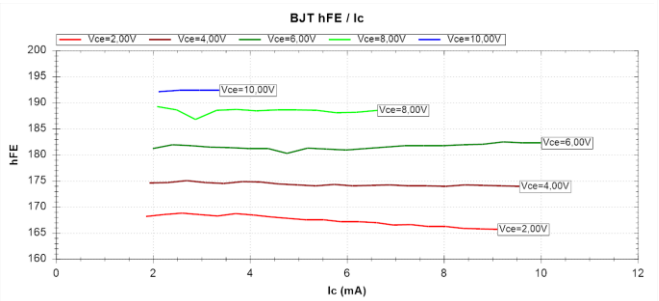
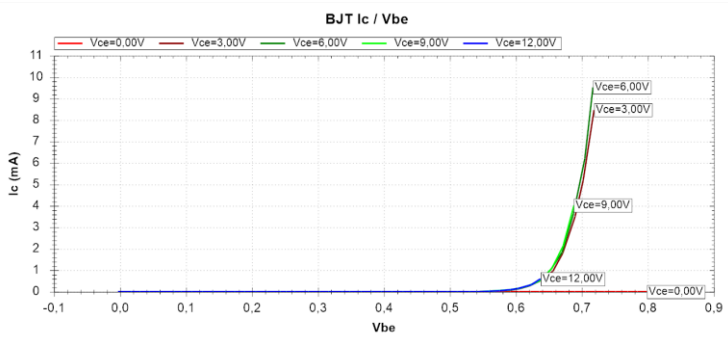
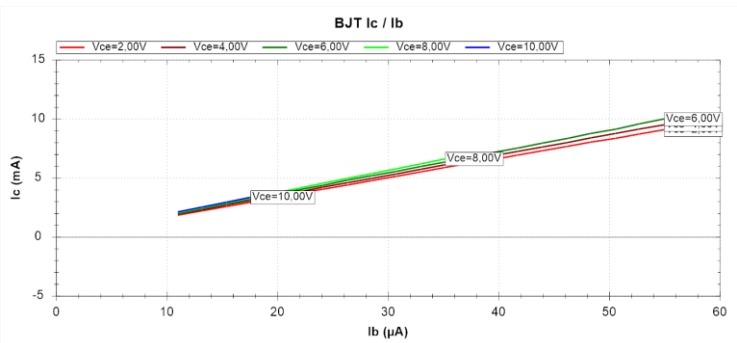
BC556A
PNP Silicon BJT
Red-E Green-B Blue-C
hFE=183 at Ic=5,00mA
Vbe=0,787V at Ib=5,00mA
VceSat=0,042V at Ic=5,0mA and Ib=1,00mA
IcLeak=0.000mA











§ Current gain (hFE) can be measured between 4 and 32000.
§ Gain accuracy for gain lower than 2000 is typically ±3% ±5hFE.
§ Gain is determined by measuring the step change in base current required to obtain a step change of collector current of 5.0mA±0.25mA. This ensures that leakage current does not influence the gain figure.
§ Saturation Voltage VceSat is measured, with a collector current of 5mA and a base current of 1mA, if the hFE is greater than 10.
§ Base-emitter voltage drop is measured at a different base current to that used for the gain measurement.
§ Base-emitter voltage accuracy is typically ±1% ±0.006V at a current of typically 5.0mA ±1.0mA.
§ If the base-emitter voltage is less than 0.55V, then it is likely that the transistor is a germanium type.
§ Leakage current of germanium types can vary hugely with small temperature variations. Even the cooling after handling (or the warming during handling) can influence the leakage current very significantly. That is normal.
§ Gain of silicon and germanium types is influenced by temperature, particularly for higher gain devices.
§ Gain will vary considerably over different collector currents.